

Hydrogen-Doped Germanium Nanomembranes for Photodetectors

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Inventors: Zhenqiang Ma, Munho Kim

The Invention

Photodetectors based on hydrogen-doped, single-crystalline germanium, including waveguide integrated photodetectors for photonic chip applications are provided. Hydrogen doping provides the single-crystalline germanium with increased radiation absorption in the near infrared region of the electromagnetic spectrum, including at wavelengths of 1550 nm and above.

Additional Information

For More Information About the Inventors

<u>Zhengiang Ma</u>

Tech Fields

Semiconductors & Integrated Circuits : Components & materials

For current licensing status, please contact Jeanine Burmania at jeanine@warf.org or 608-960-9846

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